



STL16N65M5

N-channel 650 V, 0.270 Ω , 12 A PowerFLAT™ 8x8 HV MDmesh™ V Power MOSFET

Features

Order code	V _{DSS} @ T _{Jmax}	R _{DS(on)} max	I _D
STL16N65M5	710 V	< 0.299 Ω	12 A ⁽¹⁾

1. The value is rated according to R_{thj-case}

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance

Applications

- Switching applications

Description

This device is an N-channel MDmesh™ V Power MOSFET based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

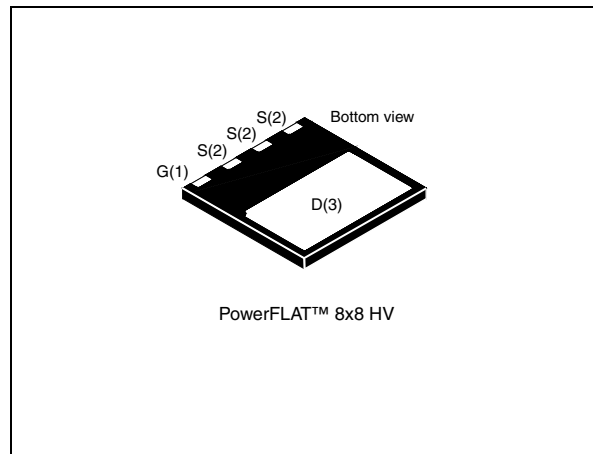


Figure 1. Internal schematic diagram

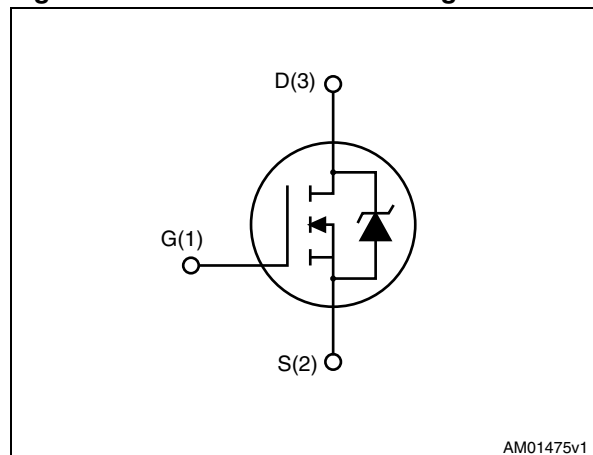


Table 1. Device summary

Order code	Marking	Package	Packaging
STL16N65M5	16N65M5	PowerFLAT™ 8x8 HV	Tape and reel

Contents

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	650	V
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	12	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	7.4	A
$I_{DM}^{(1),(2)}$	Drain current (pulsed)	48	A
$I_D^{(3)}$	Drain current (continuous) at $T_{amb} = 25\text{ }^\circ\text{C}$	2	A
$I_D^{(3)}$	Drain current (continuous) at $T_{amb} = 100\text{ }^\circ\text{C}$	1.3	A
$I_{DM}^{(2),(3)}$	Drain current (pulsed)	8	A
$P_{TOT}^{(3)}$	Total dissipation at $T_{amb} = 25\text{ }^\circ\text{C}$	3	W
$P_{TOT}^{(1)}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	90	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	4	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	200	mJ
$dv/dt^{(4)}$	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	$^\circ\text{C}$
T_j	Max. operating junction temperature	150	$^\circ\text{C}$

1. The value is rated according to $R_{thj-case}$
2. Pulse width limited by safe operating area
3. When mounted on FR-4 board of 1 inch^2 , 2oz Cu
4. $I_{SD} \leq 12\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{Peak} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1.38	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-amb max	45	$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch^2 FR-4 board, 2 oz Cu

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage ($V_{GS} = 0$)	$I_D = 1\text{ mA}$	650			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25\text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 6\text{ A}$		0.270	0.299	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}, f = 1\text{ MHz},$ $V_{GS} = 0$	-	1250	-	pF
C_{oss}	Output capacitance			30		pF
C_{rss}	Reverse transfer capacitance			3		pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }520\text{ V}, V_{GS} = 0$	-	100	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related			30		pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz open drain}$	-	2	-	Ω
Q_g	Total gate charge	$V_{DD} = 520\text{ V}, I_D = 6\text{ A},$ $V_{GS} = 10\text{ V}$ (see Figure 16)	-	31	-	nC
Q_{gs}	Gate-source charge			8		nC
Q_{gd}	Gate-drain charge			12		nC

- $C_{oss\text{ eq.}}$ time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}
- $C_{oss\text{ eq.}}$ energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
t_d (v)	Voltage delay time	$V_{DD} = 400\text{ V}$, $I_D = 8\text{ A}$,		25		ns
t_r (v)	Voltage rise time	$R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		7		ns
t_f (i)	Current fall time	(see Figure 17),	-	6	-	ns
t_c (off)	Crossing time	(see Figure 20)		8		ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current				12	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		48	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 12\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		300		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$ (see Figure 17)	-	3.5		μC
I_{RRM}	Reverse recovery current			23		A
t_{rr}	Reverse recovery time	$I_{SD} = 12\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		350		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 100\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$	-	4		μC
I_{RRM}	Reverse recovery current	(see Figure 17)		24		A

1. Pulse width limited by safe operating area

2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

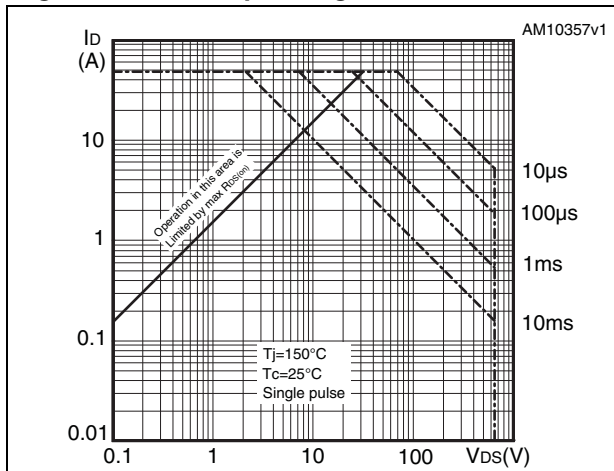


Figure 3. Thermal impedance

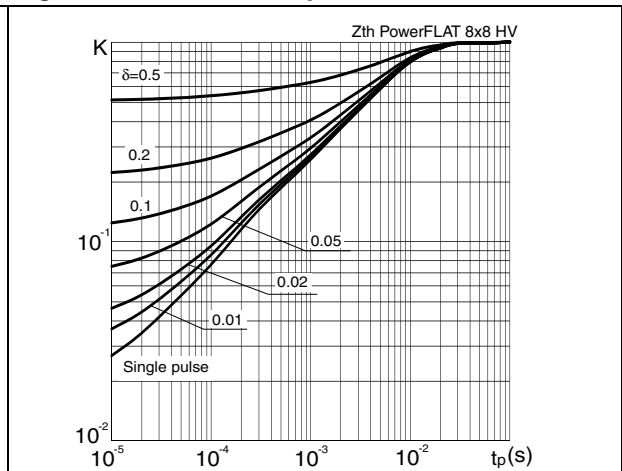


Figure 4. Output characteristics

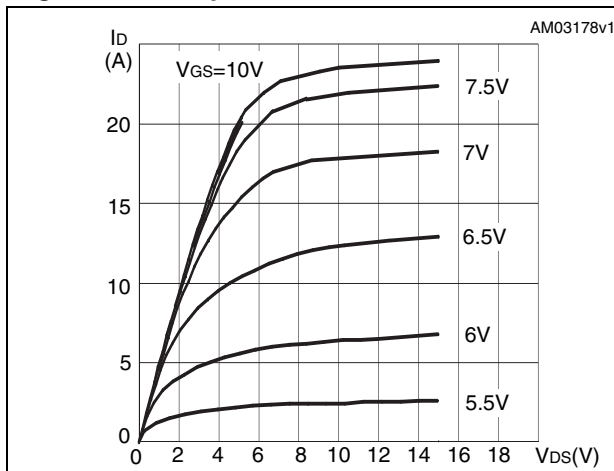


Figure 5. Transfer characteristics

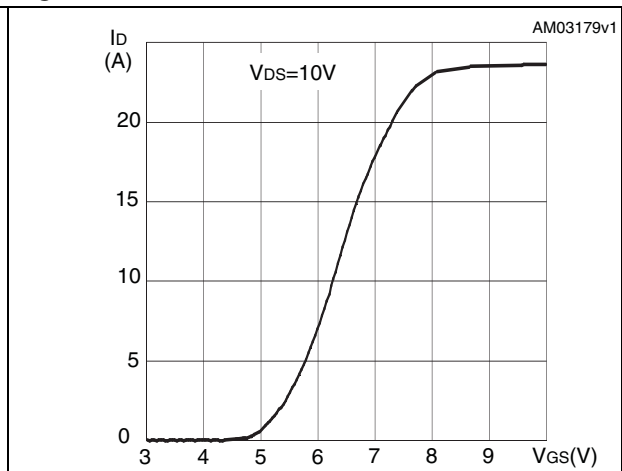


Figure 6. Normalized $B_{V_{DS}}$ vs temperature

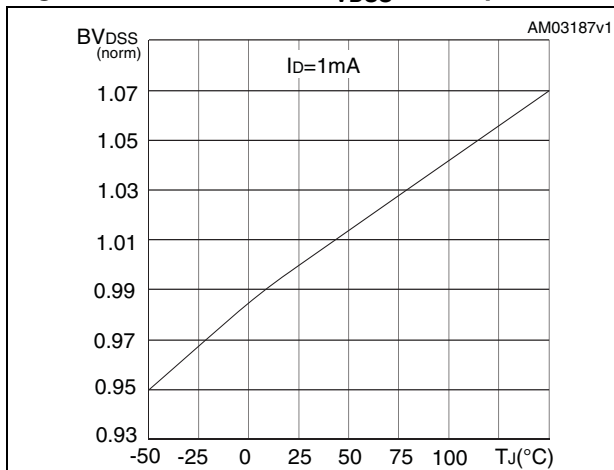


Figure 7. Static drain-source on resistance

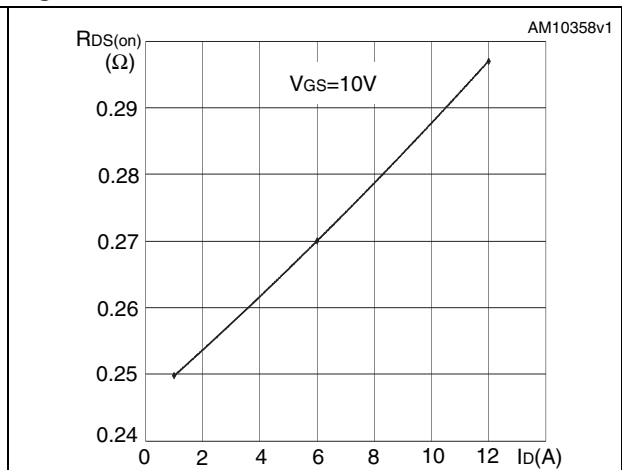


Figure 8. Output capacitance stored energy

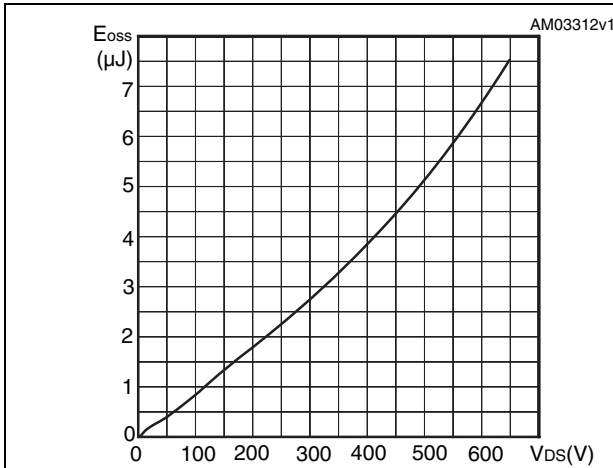


Figure 9. Capacitance variations

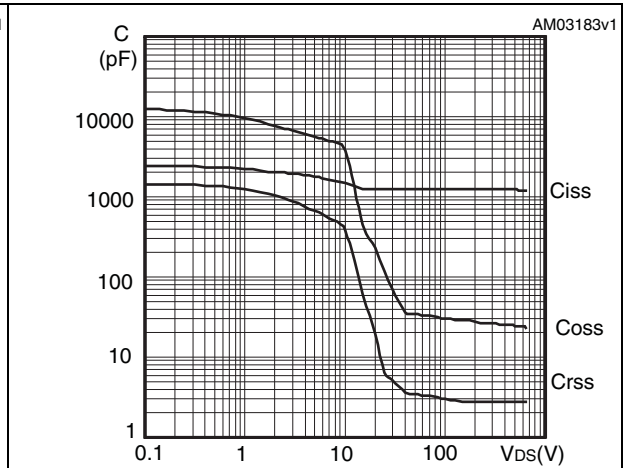


Figure 10. Gate charge vs gate-source voltage

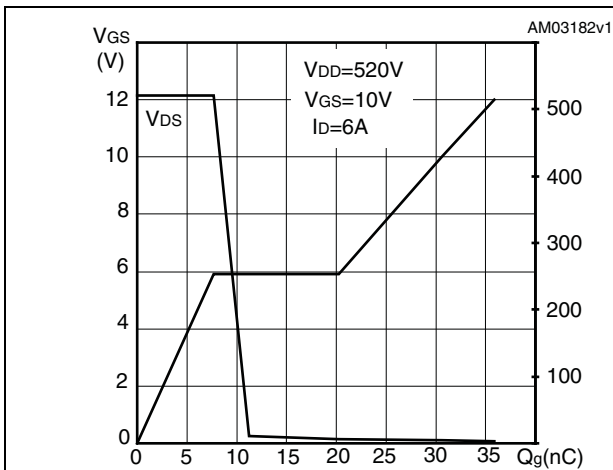


Figure 11. Normalized on resistance vs temperature

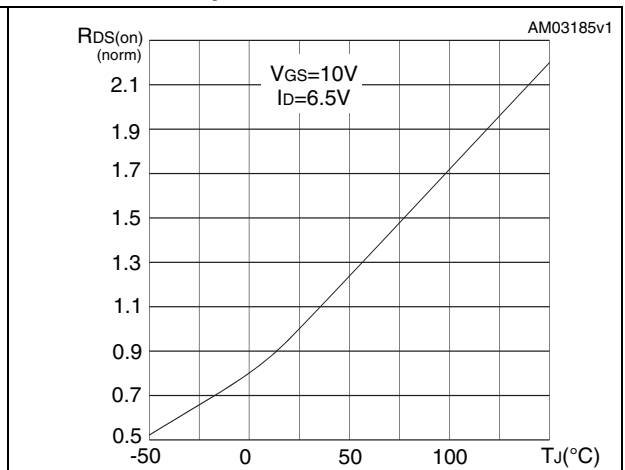


Figure 12. Normalized gate threshold voltage vs temperature

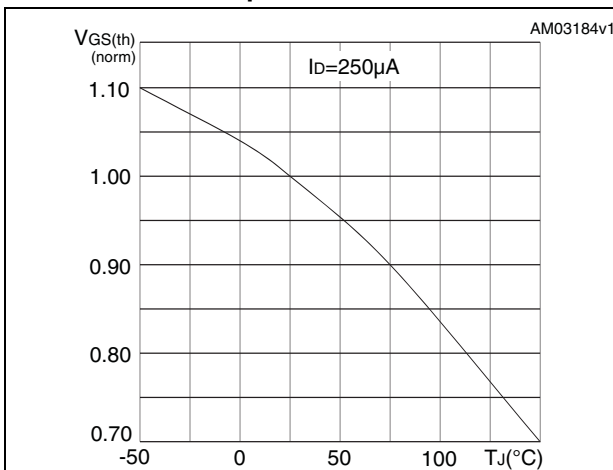


Figure 13. Source-drain diode forward characteristics

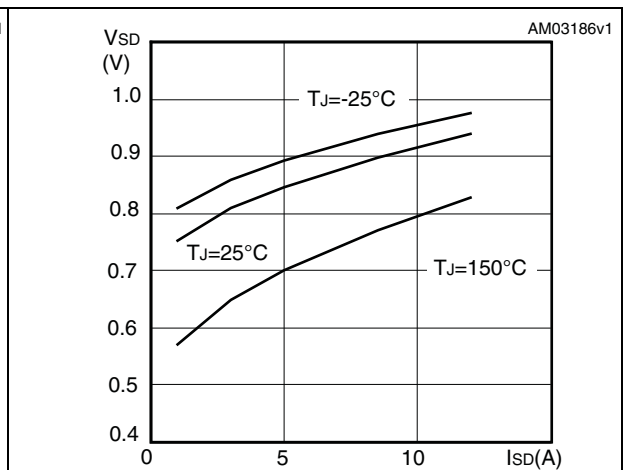
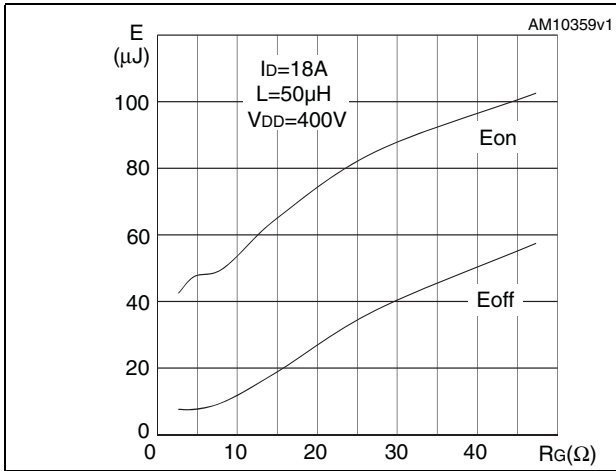


Figure 14. Switching losses vs gate resistance (1)



1. Eon including reverse recovery of a SiC diode

3 Test circuits

Figure 15. Switching times test circuit for resistive load



Figure 16. Gate charge test circuit

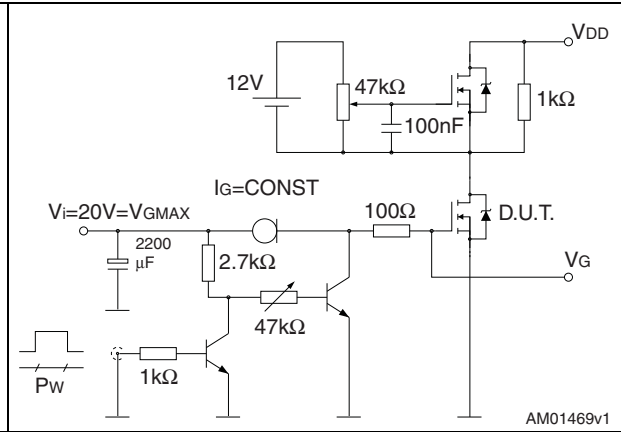


Figure 17. Test circuit for inductive load switching and diode recovery times

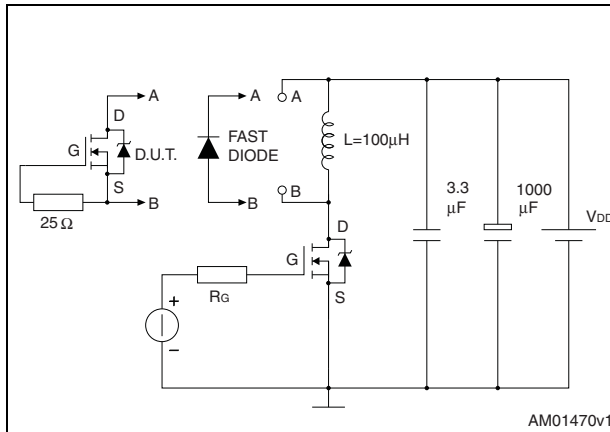


Figure 18. Unclamped inductive load test circuit

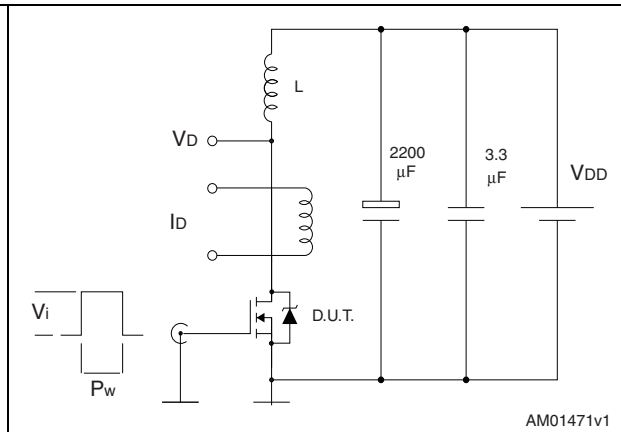


Figure 19. Unclamped inductive waveform

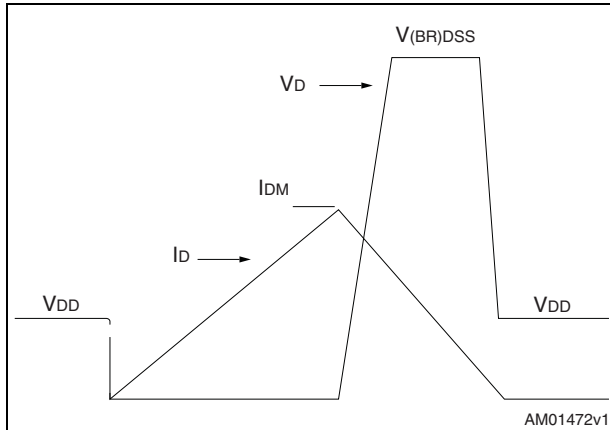
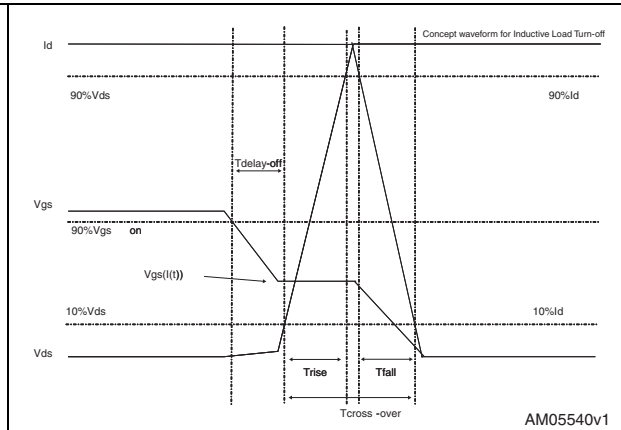


Figure 20. Switching time waveform



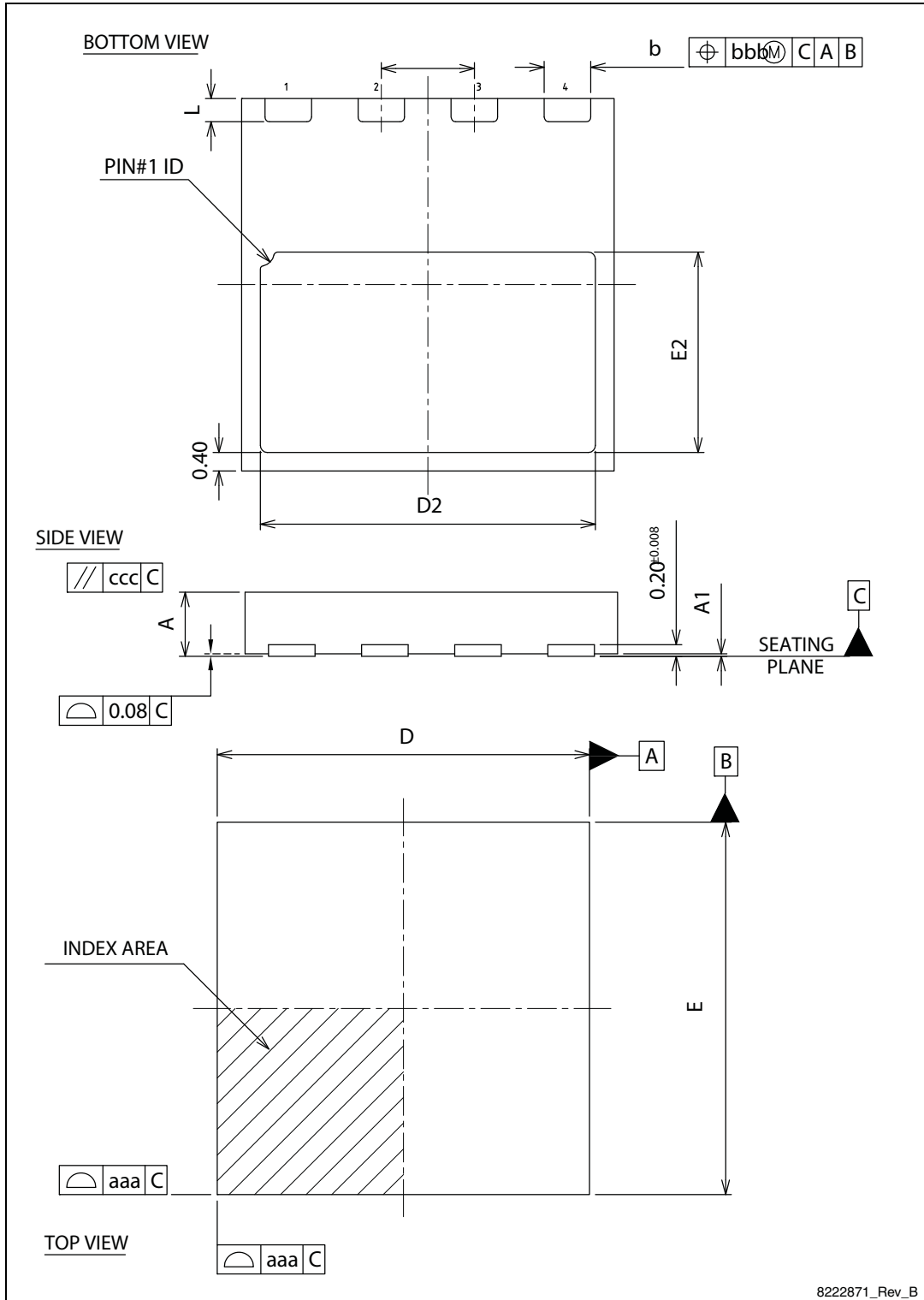
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. PowerFLAT™ 8x8 HV mechanical data

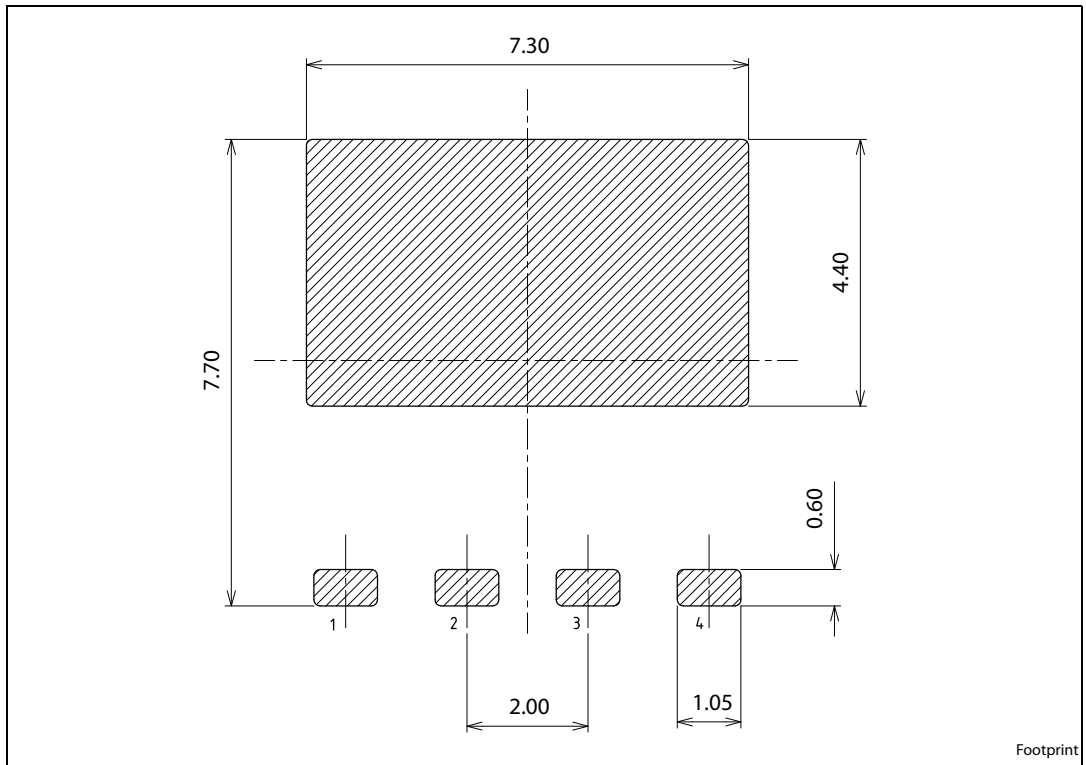
Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
b	0.95	1.00	1.05
D		8.00	
E		8.00	
D2	7.05	7.20	7.30
E2	4.15	4.30	4.40
e		2.00	
L	0.40	0.50	0.60
aaa		0.10	
bbb		0.10	
ccc		0.10	

Figure 21. PowerFLAT™ 8x8 HV drawing mechanical data



8222871_Rev_B

Figure 22. PowerFLAT™ 8x8 HV recommended footprint



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
30-Apr-2010	1	First release
08-Jun-2010	2	V_{GS} value has been changed in Table 4
10-Feb-2011	3	Modified $R_{DS(on)}$ value
28-Jul-2011	4	Document status promoted from preliminary data to datasheet Added Section 2.1: Electrical characteristics (curves) Minor text changes
03-Nov-2011	5	Section 4: Package mechanical data has been modified.

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